

J101 U.S.C.  
10/04586  
10/28/01

P

PATENT NUMBER and  
ISSUE DATE

## U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
1004586	10/29/2001	438		7823	

\*\*APPLICANTS: Park Stephen.

\*\*CONTINUING DATA VERIFIED: *See*  
 THIS APPLICATION IS A CON OF 09/493,384 01/28/2000 PAT 6,355,555

Yes

NOTE-DISCLAIMER:  
 The term of this patent shall not extend  
 beyond the expiration date  
 J.P.C. No. 6355,555

\*\* FOREIGN APPLICATIONS VERIFIED: *See*

None

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	
Foreign priority claimed	<input type="checkbox"/> yes <input checked="" type="checkbox"/> no		ATTORNEY DOCKET NO
35 USC 119 conditions met	<input type="checkbox"/> yes <input checked="" type="checkbox"/> no		2000.029996/TT3586C
Verified and Acknowledged Examiner's initials	<i>See</i>		
TITLE : Method of fabricating copper-based semiconductor devices using a sacrificial dielectric layer			

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
			Total Claims	Print Claim for O.G
ISSUE FEE		DRAWING		
Amount Due	Date Paid	Sheets Drwg.	Figs.Drwg.	Print Fig.
TERMINAL DISCLAIMER		Primary Examiner		
		PREPARED FOR ISSUE		
		Application Examiner		
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